

Description

Features

- Trench Power LV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low RDS(ON)

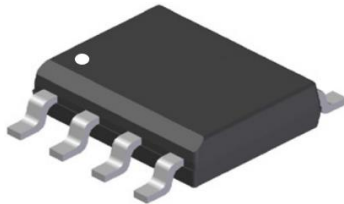
Application

- High current load application
- Load switching
- Quick Charge

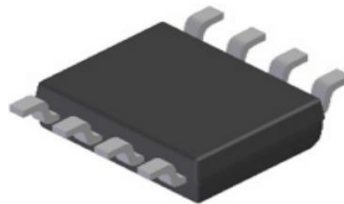
V_{DS}	-30	V
$R_{ds(on),typ}@V_{gs}=-10V$	48	mΩ
$R_{ds(on),typ}@V_{gs}=-4.5V$	78	mΩ
I_D	-5	A



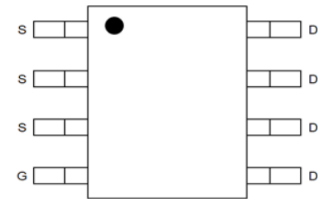
Top View



Bottom View



Pin Configuration



Package Marking and Ordering Information

Part	Marking	Package	Packing	Reel Size	Tape Width	Qty
CMT9435S	T9435S	SOP-8L	Reel	NA	NA	4000

Key Performance Parameters

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±20	V
$I_{D@Tc=25^{\circ}C}$	Continuous Drain Current, $V_{GS}=10V$	-5	A
$I_{D@Tc=100^{\circ}C}$	Continuous Drain Current, $V_{GS}=10V$	-3	A
IDM	Pulsed Drain Current ¹	-20	A
$PD@Tc=25^{\circ}C$	Total Power Dissipation	4.1	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_j	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ	Max	Units
R _{θJA}	Thermal Resistance Junction-Ambient	44	50	°C/W
R _{θJC}	Thermal Resistance Junction-Case	26	30	°C/W

Electrical Characteristics (T_J=25 °C, Unless otherwise noted)

Symbol	Parameter	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
BVDSS	Drain-Source Breakdown Voltage	--	--	-30	V	V _{GS} =0V, I _D =-250uA
R _{DS(ON)}	Static Drain-Source On-Resistance	--	48	75	mΩ	V _{GS} =-10V, I _D =-4A
		--	78	120		V _{GS} =-4.5V, I _D =-2A
V _{GS(th)}	Gate Threshold Voltage	-2.5	-1.75	-1.2	V	V _{GS} =V _{DS} , I _D =-250uA
IDSS	Drain-Source Leakage Current	--	--	1	uA	V _{DS} =-30V, V _{GS} =0V, T _J =25°C
		--	--	10	uA	V _{DS} =-30V, V _{GS} =0V, T _J =125°C
IGSS	Gate-Source Leakage Current	--	--	±100	nA	V _{GS} =±20V, V _{DS} =0V
g _{fs}	Forward Transconductance	--	8	--	S	V _{DS} =-5V, I _D =-4A
R _g	Gate Resistance	--	15	--	Ω	V _{DS} =0V, V _{GS} =0V, f=1MHz
Q _g	Total Gate Charge ^{2,3}	--	22	--	nC	V _{DS} =-15V, V _{GS} =-10V, I _D =-4A
Q _{gs}	Gate-Source Charge ^{2,3}	--	4.5	--		
Q _{gd}	Gate-Drain Charge ^{2,3}	--	9.5	--		
T _{d(on)}	Turn-On Delay Time ^{2,3}	--	35	--	ns	V _{DD} =-15V, V _{GS} =-10V, R _G =6Ω I _D =-1A
T _r	Rise Time ^{2,3}	--	18	--		
T _{d(off)}	Turn-Off Delay Time ^{2,3}	--	37	--		
T _f	Fall Time ^{2,3}	--	3.5	--		
C _{iss}	Input Capacitance	--	233	--	pF	V _{DS} =-15V, V _{GS} =0V, f=1MHz
C _{oss}	Output Capacitance	--	46	--		
C _{rss}	Reverse Transfer Capacitance	--	32	--		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Units
I _s	Continuous Source Current ¹	V _G =V _D =0V, Force Current	-5	--	A
I _{sm}	Pulsed Source Current ²		-20	--	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	-1.2	--	V

Note:

1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
3. Essentially independent of operating temperature.

Typical Performance Characteristics

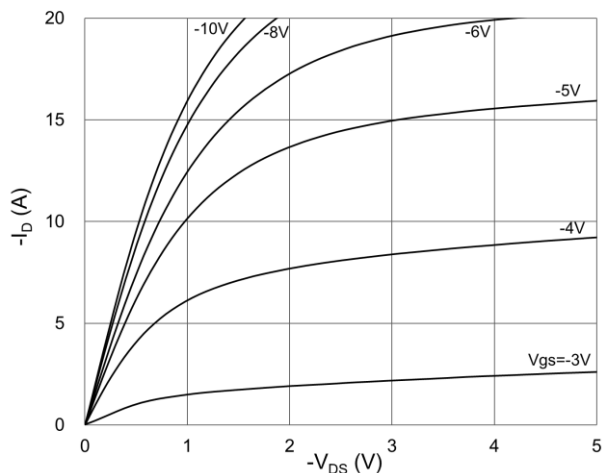
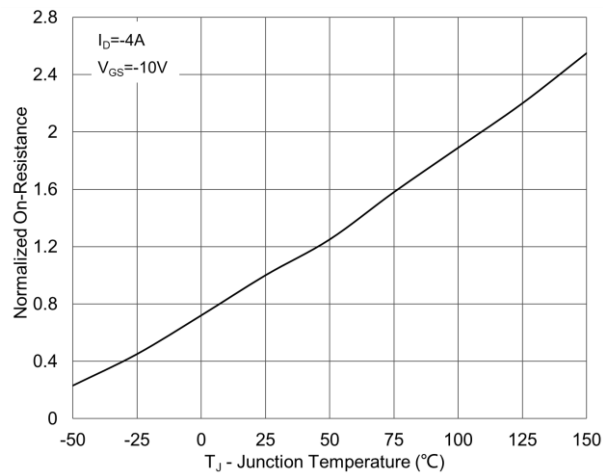
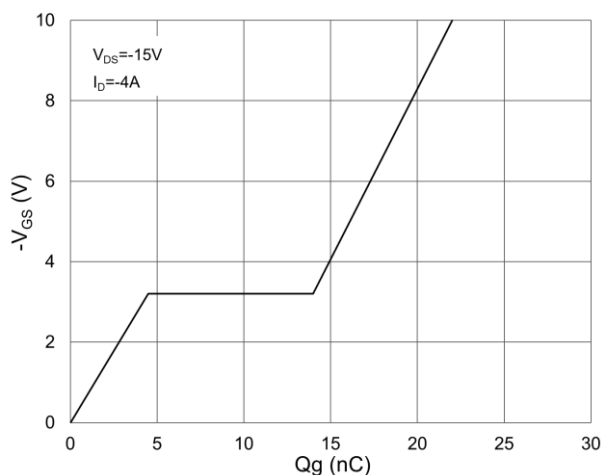
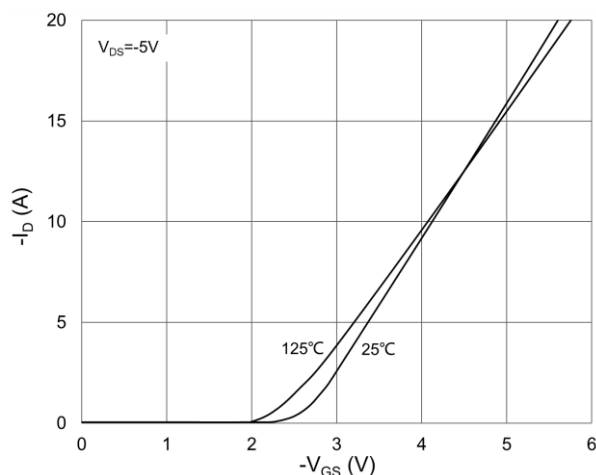
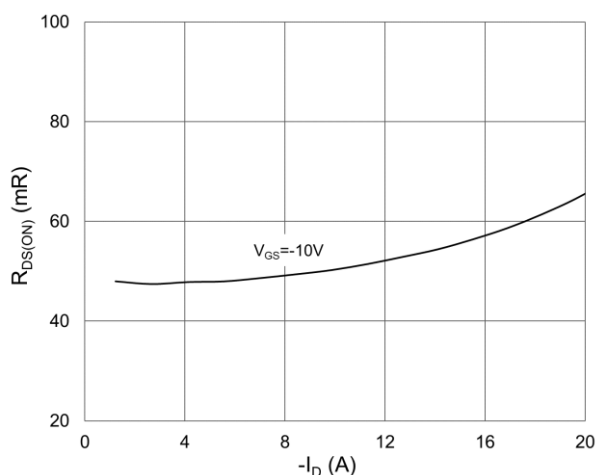
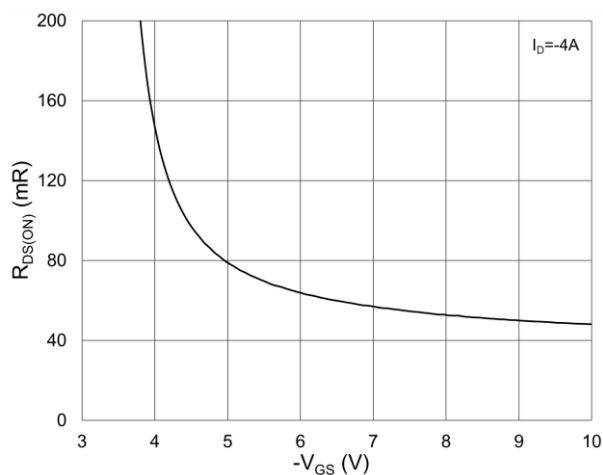
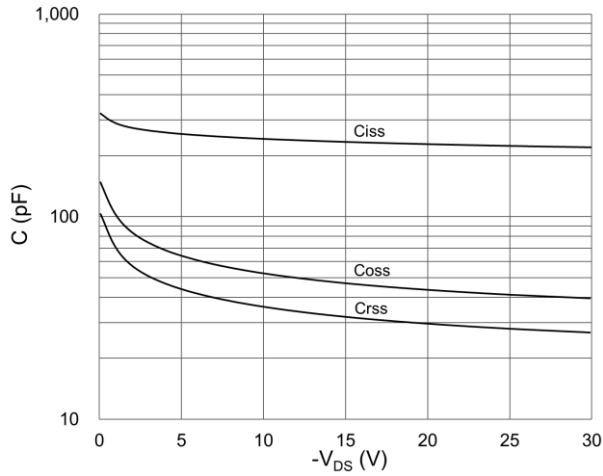
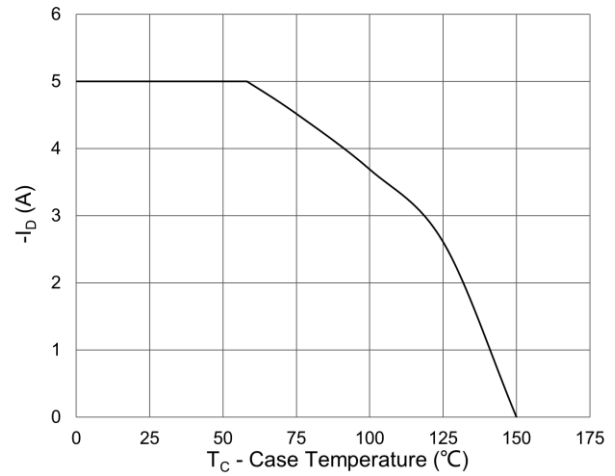
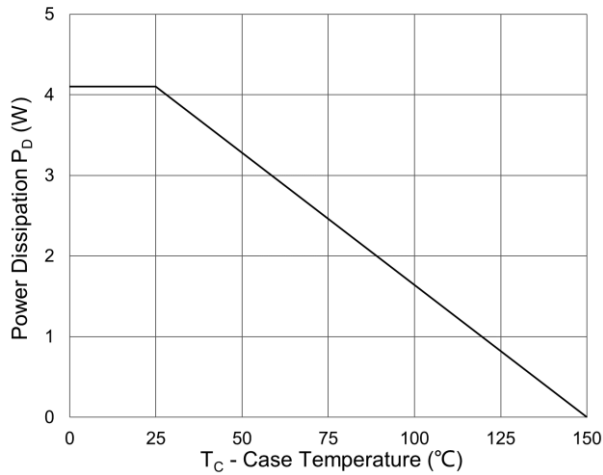
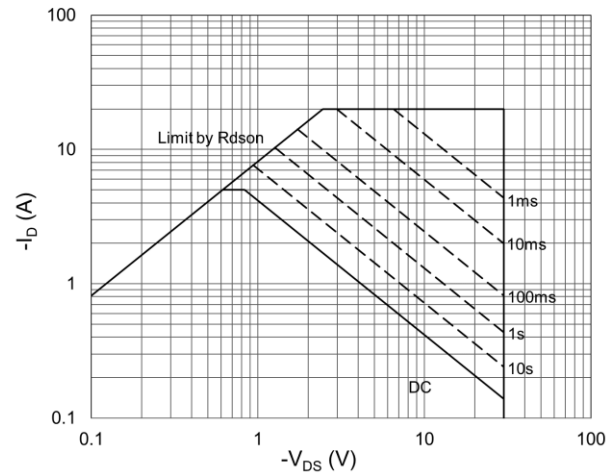
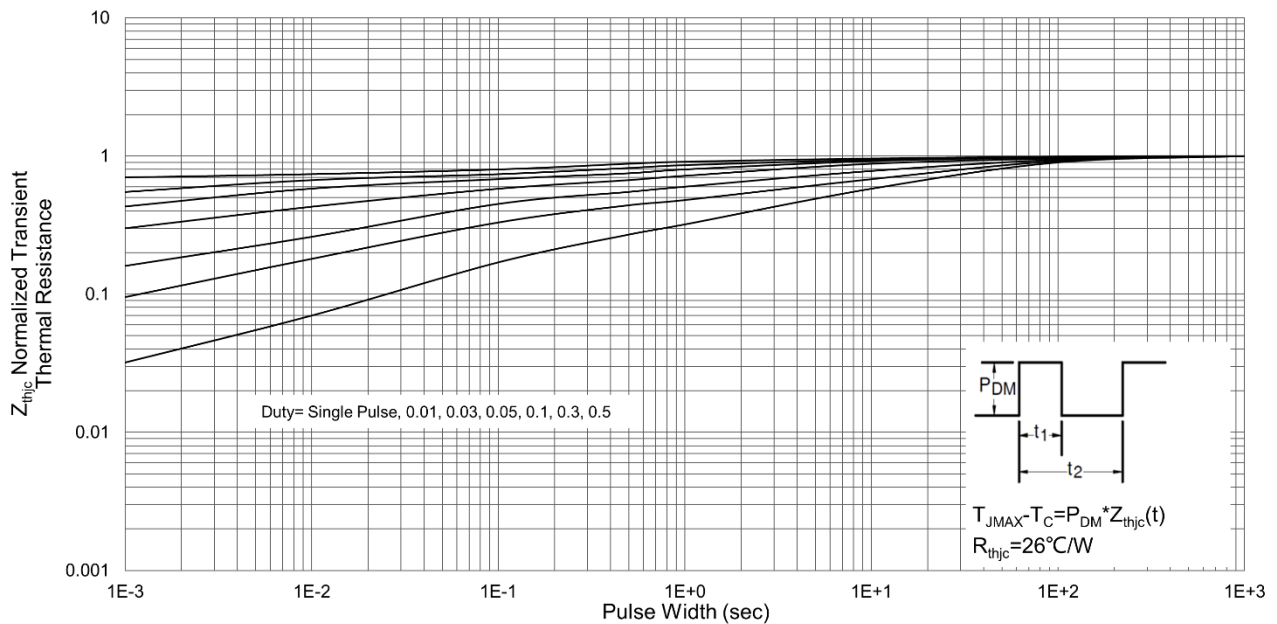
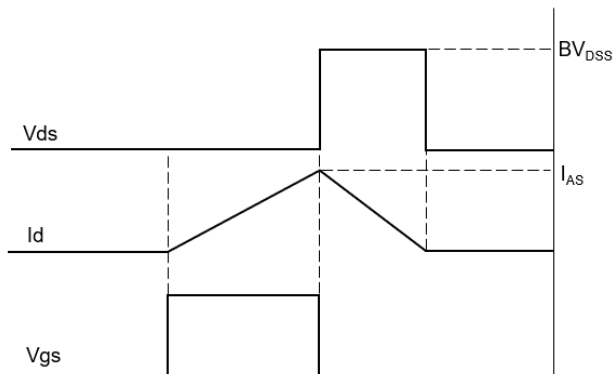
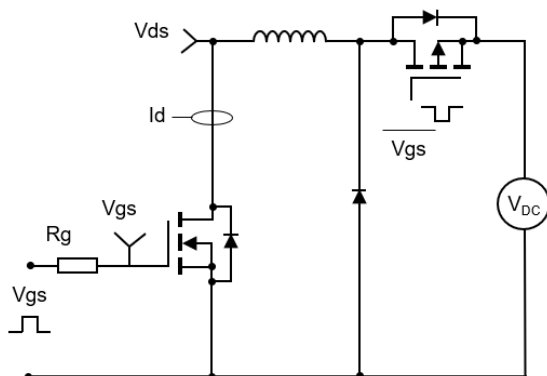
Fig1 Output Characteristics

Fig2 Normalized $R_{DS(on)}$ vs. T_J

Fig3 Gate Charge Waveform

Fig4 Transfer Characteristics

Fig5 $R_{ds(on)}$ vs. Drain Current and Gate Voltage

Fig6 $R_{ds(on)}$ vs. Gate Voltage


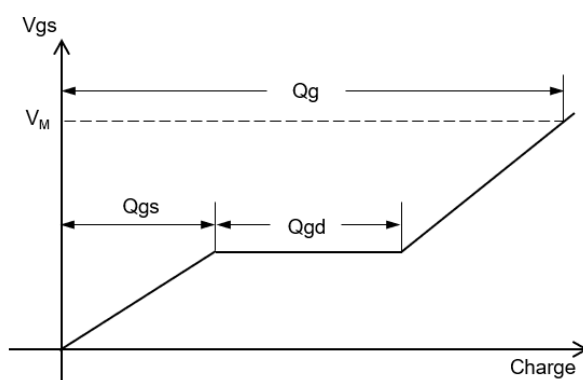
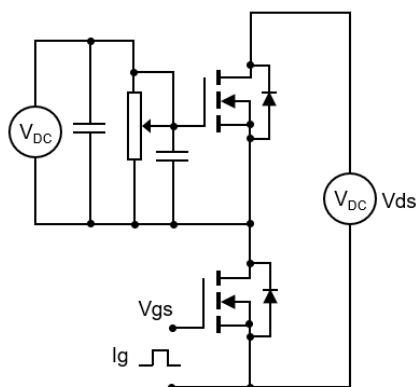
Fig7 Capacitance Characteristics

Fig8 Drain Current Derating

Fig9 Power Dissipation

Fig10 Maximum Safe Operation Area

Fig11 Normalized Transient Impedance


Test Circuit & Waveform

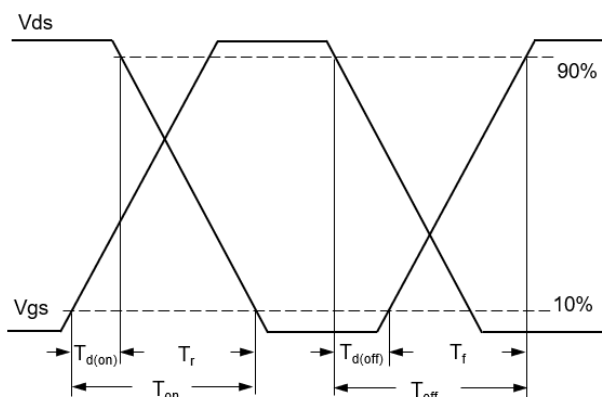
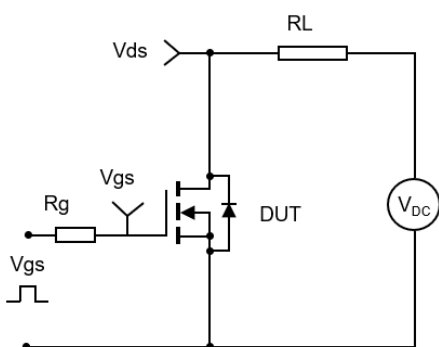
1. Unclamped Inductive Switching Test Circuit & Waveform



2. Gate Charge Test Circuit & Waveform

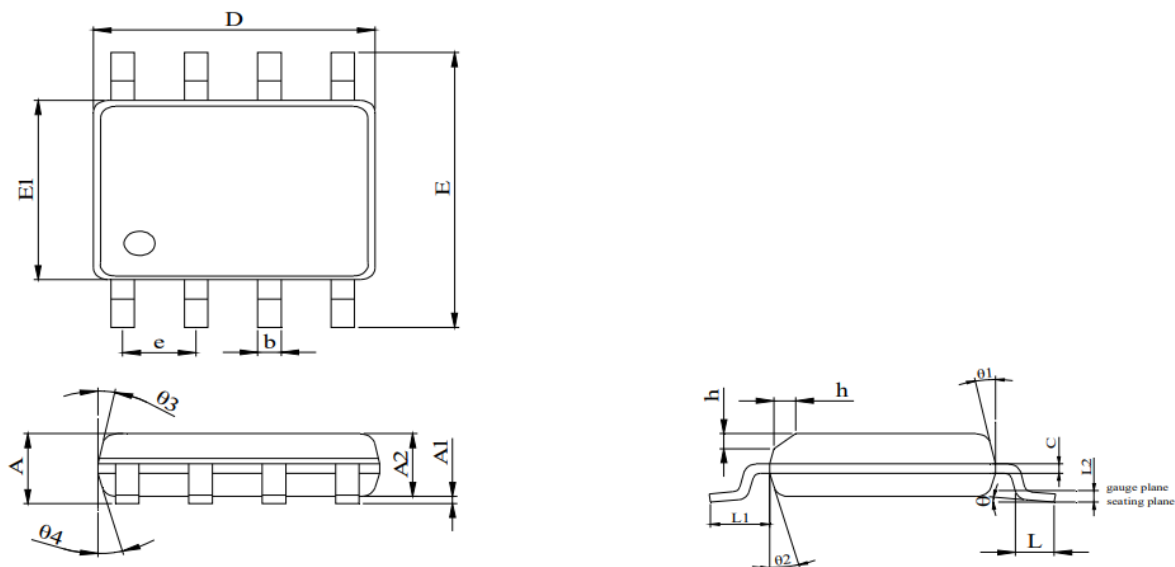


3. Resistive Switching Test Circuit & Waveform



SOP-8L Package Information

Package Outline



DIM	MILIMETER		
	MIN	MOM	MAX
A	1.35	1.50	1.65
A1	0.05	0.10	0.15
A2	1.35	1.40	1.55
b	0.38	--	0.50
c	0.17	--	0.25
D	4.70	4.90	5.10
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e	1.27(BSC)		
L	0.45	0.60	0.80
L1	1.04 REF		
L2	0.25BSC		
h	0.30	0.40	0.50
θ	0°	--	8°
θ1	10°	12°	14°
θ2	8°	10°	12°
θ3	10°	12°	14°
θ4	8°	10°	12°

Recommend Soldering Footprint

